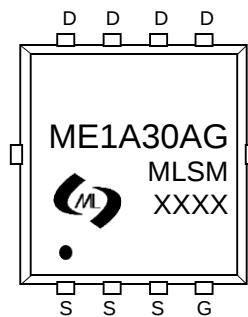


Features

- Shielded-Gate Trench(SGT) Power LV MOSFET technology
- Ultra low gate charge
- Fast switching capability
- Avalanche energy specified

Application

- Power Management in Note book
- DC/DC Converter
- LCD Display inverter

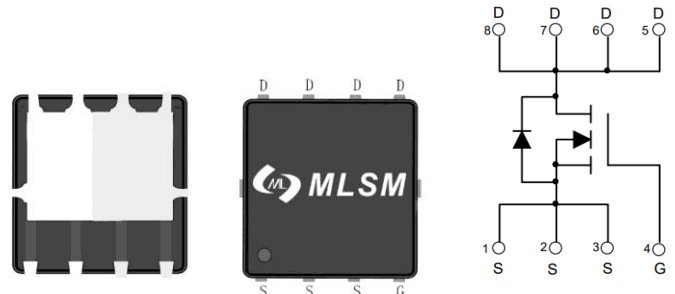


ME1A30AG: Device code
XXXX: Code

Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
100V	18mΩ@10V	30A
	25mΩ@4.5V	



PDFN3X3-8L view

Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	30	A

Mounted on Large Heat Sink

I _{DM}	Pulse Drain Current Tested		100	A
I _D	Continuous Drain Current	Tc=25°C	30	A
P _D	Maximum Power Dissipation	Tc=25°C	27	W
E _{AS}	Single pulse Avalanche Energy ^{Note1}		16	mJ

Ordering Information (Example)

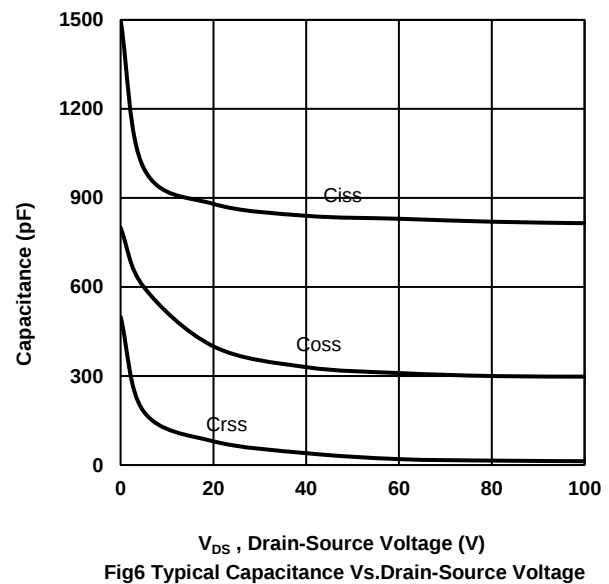
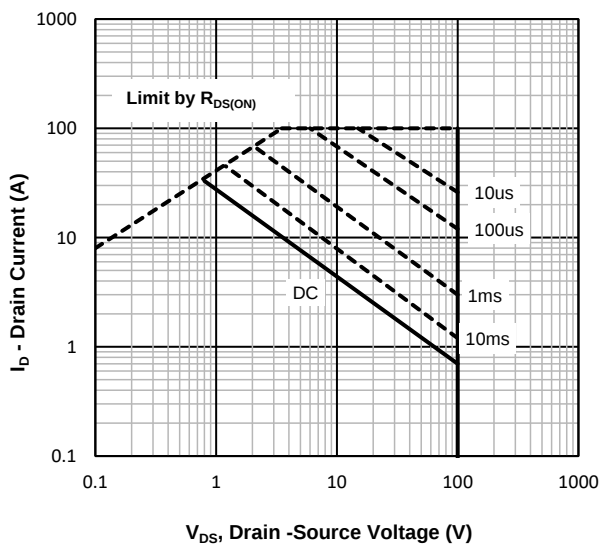
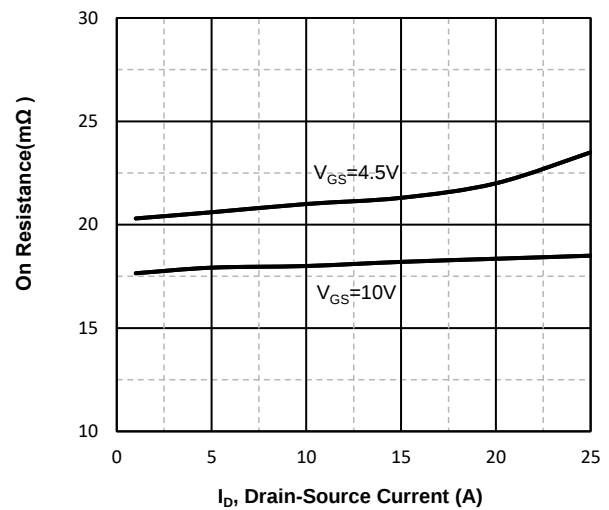
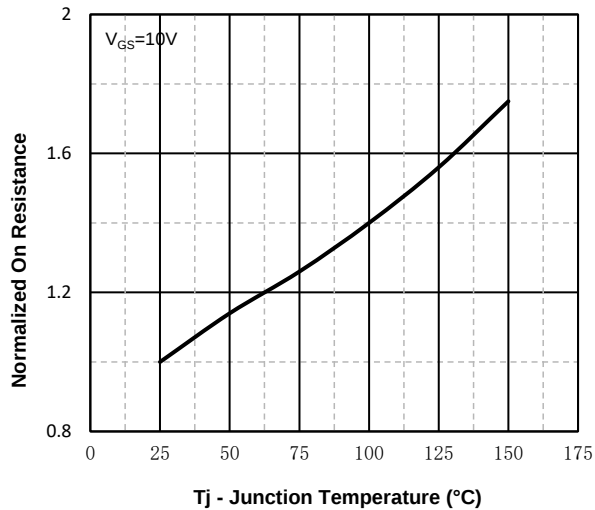
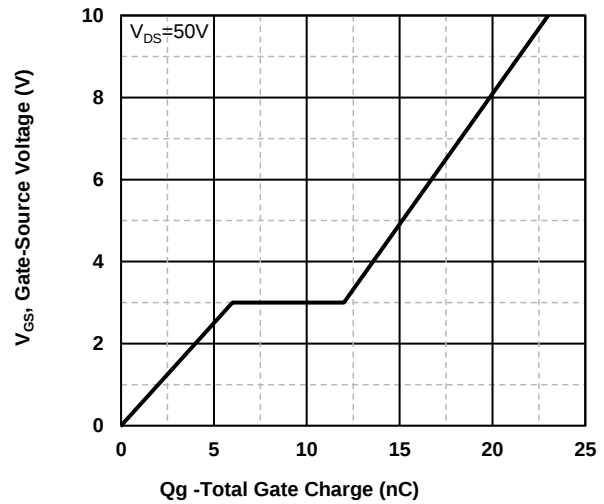
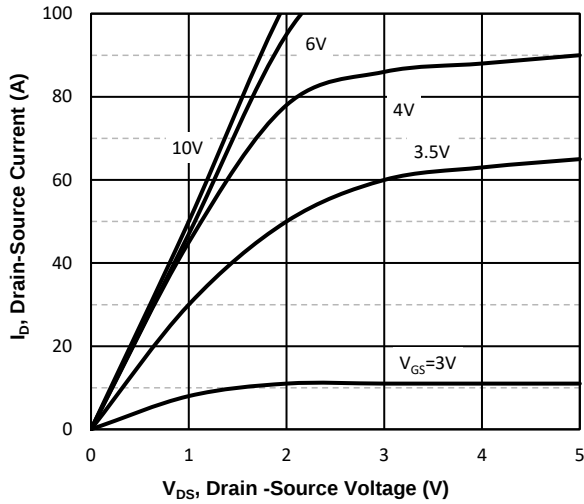
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
ME1A30AG	PDFN3X3-8L	ME1A30AG	5,000	10,000	70,000	13"reel

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V	--	--	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.2	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =30A	--	18	22	mΩ
		V _{GS} =4.5V, I _D =15A	--	25	33	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	--	820	--	pF
C _{OSS}	Output Capacitance		--	310	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	25	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =50V, I _D =20A, V _{GS} =10V	--	23	--	nC
Q _{gs}	Gate Source Charge		--	6.1	--	nC
Q _{gd}	Gate Drain Charge		--	5.5	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =50V, I _D =20A, V _{GS} =10V, R _G =3Ω	--	15	--	nS
t _r	Turn-on Rise Time		--	3.3	--	nS
t _{d(off)}	Turn-Off Delay Time		--	30	--	nS
t _f	Turn-Off Fall Time		--	7.5	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25℃, Is=30A	--	--	1.2	V

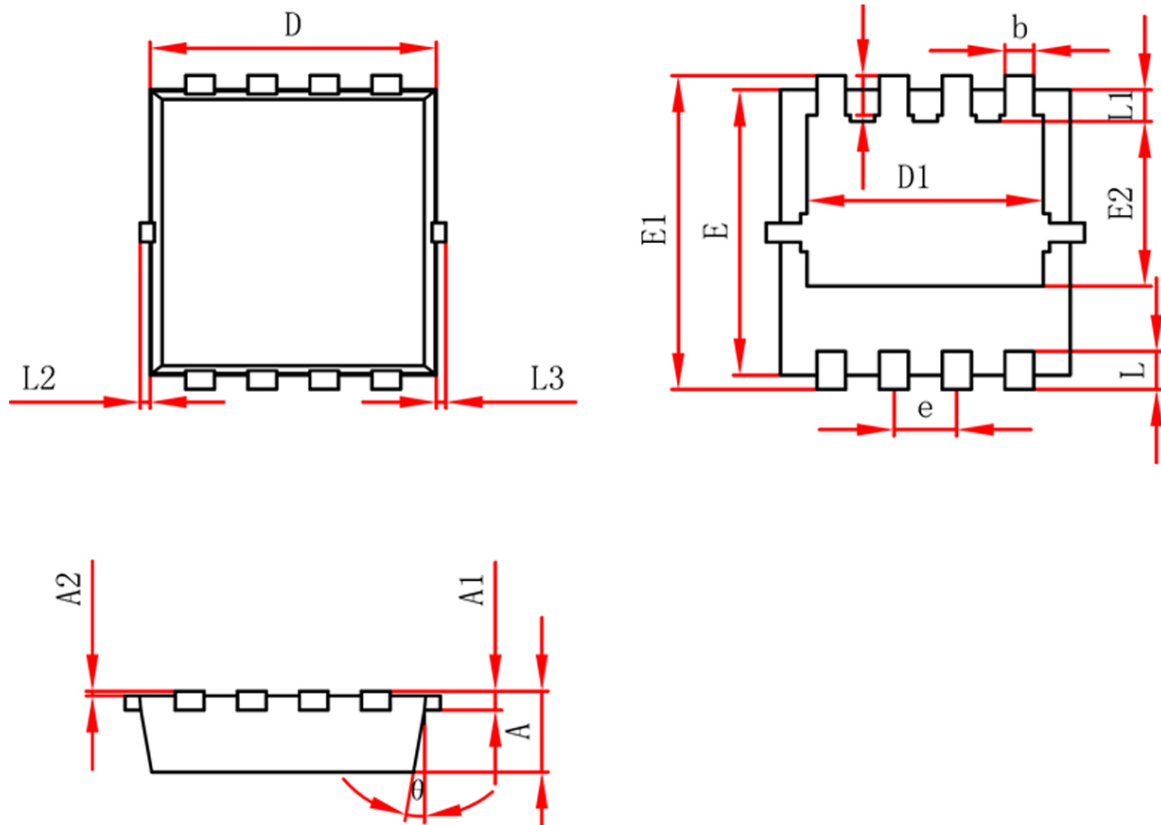
Note:

- 1、EAS Test condition: V_{DD}=50V, V_{GS}=10V, L=0.5mH, I_{AS}=8A, R_G=25Ω, Starting T_J = 25°C

Typical Operating Characteristics



PDFN3X3-8L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.750	0.850	0.030	0.034
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.950	3.150	0.117	0.125
D1	2.400	2.500	0.095	0.099
E	2.950	3.050	0.117	0.121
E1	3.250	3.350	0.129	0.132
E2	1.685	1.785	0.067	0.071
b	0.250	0.350	0.010	0.014
e	0.600	0.700	0.024	0.028
L	0.350	0.450	0.014	0.018
L1	0.325	0.425	0.013	0.017
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.365	0.465	0.014	0.018
θ	10°	12°	10°	12°